

In re application of: Ki-Yeon Park, et al. Conf. No. 8248  
Serial No. 10/713,577 Examiner: Nhu, David  
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For: CAPACITOR OF SEMICONDUCTOR MEMORY DEVICE THAT HAS  
COMPOSITE  $\text{Al}_2\text{O}_3/\text{HfO}_2$  DIELECTRIC LAYER AND METHOD OF  
MANUFACTURING THE SAME

INFORMATION DISCLOSURE CITATION  
FORM PTO-1449 (Modified)

U.S. PATENT DOCUMENTS

Exam Init	Ref	Document Number	Issue Date	Name	Class	Sub Class
<u>PN</u>		5,440,157	Aug. 1995	Imai et al.		
		5,641,702	Jun. 1997	Imai et al.		
		6,287,965	Sep. 2001	Kang et al.		
		6,399,491	Jun. 2002	Jeon et al.		
		6,596,583	Jul. 2003	Agarwal et al.		
		6,599,794	Jul. 2003	Kiyotoshi et al.		
		6,660,631	Dec. 2003	Marsh, EugeneP.		
<u>PN</u>		6,660,660	Dec. 2003	Kauka et al.		

INFORMATION DISCLOSURE CITATION  
FORM PTO-1449 (Modified)

FOREIGN PATENT DOCUMENTS

Exam Init	Ref	Publication Number	Publication Date	Country	Name

OTHER DOCUMENTS

Exam Init	Ref	Author, Title, Date, Pertinent Pages, Etc.)

Examiner: *[Signature]*

Date Considered: 2/28/05